

REVISIONS

LTR	DESCRIPTION	DATE (YR-MO-DA)	APPROVED
A	Add device types 03, 04, and Appendix A. Make change to description title block by adding the word "BIPOLAR". Delete Accelerated annealing test paragraph 4.4.4.1.1. - ro	14-07-09	C. SAFFLE
B	Make changes to Table IIB. - ro	15-02-18	C. SAFFLE
C	Update document paragraphs to current MIL-PRF-38535 requirements. - ro	20-05-12	J. ESCHMEYER



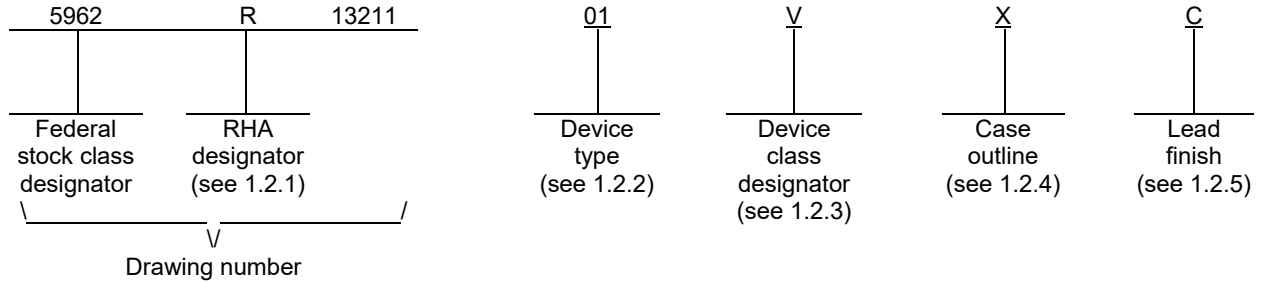
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PMIC N/A	PREPARED BY RICK OFFICER	<p align="center">DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990 https://www.dla.mil/LandandMaritime</p>																	
<p align="center">STANDARD MICROCIRCUIT DRAWING</p> <p>THIS DRAWING IS AVAILABLE FOR USE BY ALL DEPARTMENTS AND AGENCIES OF THE DEPARTMENT OF DEFENSE</p> <p align="center">AMSC N/A</p>	CHECKED BY RAJESH PITHADIA																		
	APPROVED BY CHARLES F. SAFFLE	MICROCIRCUIT, LINEAR, BIPOLAR, ULTRA LOW NOISE, PRECISION VOLTAGE REFERENCE, MONOLITHIC SILICON																	
	DRAWING APPROVAL DATE 13-12-17																		
	REVISION LEVEL C	SIZE A CAGE CODE 67268 5962-13211																	
		SHEET 1 OF 20																	

1. SCOPE

1.1 Scope. This drawing documents two product assurance class levels consisting of high reliability (device class Q) and space application (device class V). A choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). When available, a choice of Radiation Hardness Assurance (RHA) levels is reflected in the PIN.

1.2 PIN. The PIN is as shown in the following example:



1.2.1 RHA designator. Device classes Q and V RHA marked devices meet the MIL-PRF-38535 specified RHA levels and are marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.

1.2.2 Device type(s). The device type(s) identify the circuit function as follows:

<u>Device type</u>	<u>Generic number</u>	<u>Voltage reference output</u>	<u>Circuit function</u>
01	ISL71090SEH-12	1.25 V	Radiation hardened ultra low noise, precision voltage reference
02	ISL71090SEH-25	2.5 V	Radiation hardened ultra low noise, precision voltage reference
03	ISL71090SEH-50	5.0 V	Radiation hardened ultra low noise, precision voltage reference
04	ISL71090SEH-75	7.5 V	Radiation hardened ultra low noise, precision voltage reference

1.2.3 Device class designator. The device class designator is a single letter identifying the product assurance level as follows:

<u>Device class</u>	<u>Device requirements documentation</u>
Q or V	Certification and qualification to MIL-PRF-38535

1.2.4 Case outline(s). The case outline(s) are as designated in MIL-STD-1835 and as follows:

<u>Outline letter</u>	<u>Descriptive designator</u>	<u>Terminals</u>	<u>Package style</u>
X	See figure 1	8	Dual flat pack

1.2.5 Lead finish. The lead finish is as specified in MIL-PRF-38535 for device classes Q and V.

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1.3 Absolute maximum ratings. ^{1/}

Maximum voltage:

V _{IN} to GND	-0.5 V to +40 V
V _{IN} to GND at an LET = 86 MeV/(mg/cm ²)	-0.5 V to +36 V
V _{OUT} to GND (10 seconds)	-0.5 V to V _{OUT} + 0.5 V
Voltage on any pin to ground	-0.5 V to +V _{OUT} + 0.5 V
Voltage on DNC pins	No connections permitted to these pins
Input voltage slew rate (maximum)	0.1 V/μs
Maximum junction temperature (T _{JMAX})	150°C
Continuous power dissipation (P _D) :	
T _A = +125°C	178 mW
T _A = +25°C	892 mW
Storage temperature range (T _{STG})	-65°C to +150°C
Thermal resistance, junction to case (θ _{JC})	15°C/W ^{2/}
Thermal resistance, junction to ambient (θ _{JA})	140°C/W ^{3/}

1.4 Recommended operating conditions.

Input voltage (V_{IN}):

Device types 01 and 02	4 V to +30 V
Device type 03	7 V to +30 V
Device type 04	9.2 V to +30 V
Operating free-air temperature range (T _A)	-55°C to +125°C

1.5 Radiation features.

Maximum total dose available (dose rate = 50 – 300 rads(Si)/s) :

Device types 01, 02, 03 and 04	100 krad(Si) ^{4/}
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Maximum total dose available (dose rate ≤ .010 rad(Si)/s):

Device types 01, 02, 03 and 04	50 krad(Si) ^{4/}
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Single event phenomenon (SEP):

No Single event latchup (SEL) occurs at effective LET (see 4.4.4.2)	≤ 86 MeV/(mg/cm ²) ^{5/}
No Single event burnout (SEB) occurs at effective LET (see 4.4.4.2)	≤ 86 MeV/(mg/cm ²) ^{5/}
Single event transients (SET) observed at LET (see 4.4.4.2)	86 MeV/(mg/cm ²) ^{5/}
(Resulted recovery time not exceeding 50μs at saturated cross section = 1.48 x 10 ⁻⁴ cm ²)	

- ^{1/} Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.
- ^{2/} For θ_{JC}, the “case temperature” location is the center of the ceramic on the package underside.
- ^{3/} θ_{JA} is measured with the component mounted on a high effective thermal conductivity test board in free air.
- ^{4/} Device types 01, 02, 03, and 04 radiation end point limits for the noted parameters are guaranteed only for the conditions as specified in MIL-STD-883, method 1019, condition A to a maximum total dose of 100 krad(Si), and condition D to a maximum total dose of 50 krad(Si).
- ^{5/} Limits are characterized at initial qualification and after any design or process changes which may affect the SEP characteristics but are not production tested unless specified by the customer through the purchase order or contract. See manufacturer’s SEE test report and table IB for more information.

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2. APPLICABLE DOCUMENTS

2.1 Government specification, standards, and handbooks. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATION

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

DEPARTMENT OF DEFENSE STANDARDS

MIL-STD-883 - Test Method Standard Microcircuits.
MIL-STD-1835 - Interface Standard Electronic Component Case Outlines.

DEPARTMENT OF DEFENSE HANDBOOKS

MIL-HDBK-103 - List of Standard Microcircuit Drawings.
MIL-HDBK-780 - Standard Microcircuit Drawings.

(Copies of these documents are available online at <https://quicksearch.dla.mil>.)

2.2 Non-Government publications. The following document(s) form a part of this document to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

ASTM INTERNATIONAL (ASTM)

ASTM F1192 - Standard Guide for the Measurement of Single Event Phenomena (SEP) from Heavy Ion Irradiation of semiconductor Devices.

(Copies of these documents are available online at <https://www.astm.org>.)

2.3 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

3.1 Item requirements. The individual item requirements for device classes Q and V shall be in accordance with MIL-PRF-38535 as specified herein, or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein.

3.1.1 Microcircuit die. For the requirements of microcircuit die, see appendix A to this document.

3.2 Design, construction, and physical dimensions. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein for device classes Q and V.

3.2.1 Case outline. The case outline shall be in accordance with 1.2.4 herein and figure 1.

3.2.2 Terminal connections. The terminal connections shall be as specified on figure 2.

3.2.3 Radiation exposure circuit. The radiation exposure circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing and acquiring activity upon request.

3.3 Electrical performance characteristics and postirradiation parameter limits. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table IA and shall apply over the full ambient operating temperature range.

3.4 Electrical test requirements. The electrical test requirements shall be the subgroups specified in table IIA. The electrical tests for each subgroup are defined in table IA.

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TABLE IA. Electrical performance characteristics.

Test	Symbol	Conditions <u>1/ 2/</u> -55°C ≤ TA ≤ +125°C unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	
VOUT accuracy <u>3/</u>	VOA	VOUT = 1.252 V	1	01	-0.05	+0.05	%
			2,3		-0.15	+0.15	
			M,D,P,L,R		1	-0.15	
		VOUT = 2.5 V	1	02	-0.05	+0.05	
			2,3		-0.15	+0.15	
			M,D,P,L,R		1	-0.175	
		VOUT = 5.005 V	1	03	-0.05	+0.05	
			2,3		-0.15	+0.15	
			M,D,P,L,R		1	-0.3	
		VOUT = 7.5 V	1	04	-0.05	+0.05	
			2,3		-0.15	+0.15	
			M,D,P,L,R		1	+0.3	
Output voltage temperature <u>4/</u> coefficient	TCVOUT		1,2,3	01, 02, 03, 04		10	ppm/°C
Input voltage range <u>5/</u>	VIN	VOUT = 1.252 V	1,2,3	01	4.0	30	V
		VOUT = 2.5 V		02	4.0	30	
		VOUT = 5.005 V		03	7.0	30	
		VOUT = 7.5 V		04	9.2	30	
Supply current	IIN		1,2,3	01, 02		1.28	mA
				03, 04		1.5	
Line regulation	$\Delta V_{OUT}/$ ΔV_{IN}	VIN = 4.0 V to 30 V, VOUT = 1.252 V	1,2,3	01		18	ppm/V
		VIN = 4.0 V to 30 V, VOUT = 2.5 V		02		18	
		VIN = 7.0 V to 30 V, VOUT = 5.005 V		03		20	
		VIN = 9.2 V to 30 V, VOUT = 7.5 V		04		20	

See footnotes at end of table.

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TABLE IA. Electrical performance characteristics – Continued.

Test	Symbol	Conditions <u>1/ 2/</u> -55°C ≤ TA ≤ +125°C unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	
Load regulation	ΔV _{OUT} / ΔI _{OUT}	Sourcing: 0 mA ≤ I _{OUT} ≤ 20 mA	1,2,3	01		55	ppm/mA
				02		35	
				03		20	
				04		20	
		Sinking: -10 mA ≤ I _{OUT} ≤ 0 mA		02		70	
				03		40	
				04		40	
Dropout voltage <u>6/</u>	V _D	V _{OUT} = 1.252 V at 10 mA	1,2,3	01		2.25	V
		V _{OUT} = 2.5 V at 10 mA		02		1.7	
		V _{OUT} = 5.005 V at 10 mA		03		1.7	
		V _{OUT} = 7.5 V at 10 mA		04		1.7	

- 1/ Unless otherwise specified, V_{IN} = 5 V and I_{OUT} = 0 for device types 01 and 02, V_{IN} = 10 V and I_{OUT} = 0 for device type 03, and V_{IN} = 15 V and I_{OUT} = 0 for device type 04. C_L = 0.1 μF and C_C = 1 nF for device types 01, 02, 03, and 04.
- 2/ RHA device types 01, 02, 03 and 04 supplied to this drawing will meet all levels M, D, P, L, and R of irradiation for condition A and levels M, D, P, and L for condition D. However, device types 01, 02, 03, and 04 are only tested at the R level in accordance with MIL-STD-883, method 1019, condition A and tested at the L level in accordance with MIL-STD-883, method 1019, condition D (see 1.5 herein). Pre and Post irradiation values are identical unless otherwise specified in Table IA. When performing post irradiation electrical measurements for any RHA level, T_A = +25°C.
- 3/ Post reflow drift can be normally 100 μV based on experimental results with devices on FR4 double sided boards. The customer must take this into account when considering the reference voltage after assembly.
- 4/ Over the specified temperature range. Temperature coefficient is measured by the box method whereby the change in V_{OUT} is divided by the temperature range; in this case, -55°C to +125°C = +180°C. This parameter is guaranteed but not tested. This parameter is characterized upon initial design or process changes which affect this characteristic.
- 5/ V_{IN} – V_{OUT} measured at the point where V_{OUT} drops 1 mV from the nominal measured value.
- 6/ Dropout voltage is the minimum V_{IN} – V_{OUT} differential voltage measured at the point where V_{OUT} drops 1 mV from V_{IN} = nominal at T_A = +25°C.

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TABLE IB. SEP test limits. 1/ 2/ 3/

Device types	SEP	Temperature (TA)	Effective linear energy transfer (LET)
01, 02,	No SEL	+125°C	$\leq 86 \text{ MeV}/(\text{mg}/\text{cm}^2)$
03, 04	No SEB	+125°C	$\leq 86 \text{ MeV}/(\text{mg}/\text{cm}^2)$
	SET Observed 4/	+25°C	$86 \text{ MeV}/(\text{mg}/\text{cm}^2)$

1/ For single event phenomena (SEP) test conditions, see 4.4.4.2 herein.

2/ Technology characterization and model verification supplemented by in-line data may be used in lieu of end of line testing. Test plan must be approved by the technical review board and qualifying activity.

3/ Limits are characterized at initial qualification and after any design or process changes which may affect the SEP characteristics but are not production tested unless specified by the customer through the purchase order or contract. See manufacturer's SEE test report for more information.

4/ Single event transients (SET) observed that resulted in a recovery time not exceeding 50 μs at saturated cross section = $1.48 \times 10^{-4} \text{ cm}^2$ with effective LET= $86 \text{ MeV}/(\text{mg}/\text{cm}^2)$. See manufacturer's SEE test report for more information.

3.5 Marking. The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked. For packages where marking of the entire SMD PIN number is not feasible due to space limitations, the manufacturer has the option of not marking the "5962-" on the device. For RHA product using this option, the RHA designator shall still be marked. Marking for device classes Q and V shall be in accordance with MIL-PRF-38535.

3.5.1 Certification/compliance mark. The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-PRF-38535.

3.6 Certificate of compliance. For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.6.1 herein). The certificate of compliance submitted to DLA Land and Maritime-VA prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device classes Q and V, the requirements of MIL-PRF-38535 and herein.

3.7 Certificate of conformance. A certificate of conformance as required for device classes Q and V in MIL-PRF-38535 shall be provided with each lot of microcircuits delivered to this drawing.

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Case X

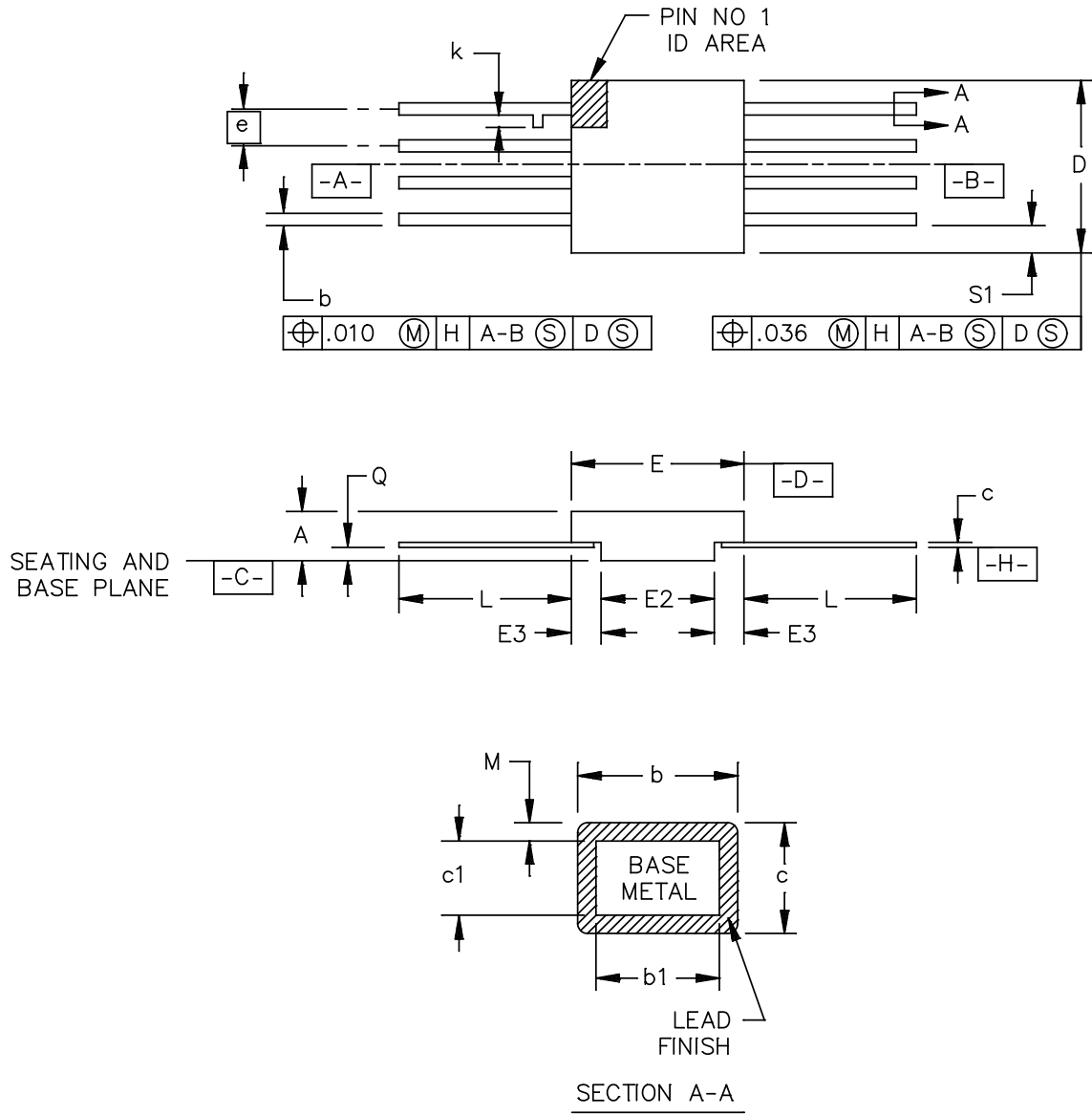


FIGURE 1. Case outline.

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DLA LAND AND MARITIME
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Case X – continued.

Symbol	Inches		Millimeters		Notes
	Min	Max	Min	Max	
A	0.087	0.110	2.21	2.79	
b	0.015	0.022	0.38	0.56	
b1	0.015	0.019	0.38	0.48	
c	0.004	0.009	0.10	0.23	
c1	0.004	0.007	0.10	0.18	
D	0.245	0.265	6.22	6.73	
E	0.245	0.265	6.22	6.73	
E2	0.170	0.180	4.32	4.57	
E3	0.030	---	0.76	---	7
e	0.050 BSC		1.27 BSC		
k	0.008	0.015	0.20	0.38	3
L	0.325	0.370	8.26	9.40	
Q	0.026	0.036	0.66	0.92	8
S1	0.005	---	0.13	---	6
M	---	0.0015	---	0.04	
N	8		8		

NOTES:

1. The U.S. government preferred system of measurement is the metric SI system. However, since this item was originally designed using inch-pound units of measurement, in the event of conflict between the metric and inch-pound units, the inch-pound units shall take precedence.
2. Index area: A notch or a pin one identification mark shall be located adjacent to pin one and shall be located within the shaded area shown. Alternately, a tab (dimension k) may be used to identify pin one.
3. If a pin one identification mark is used in addition to a tab, the limits of dimension k do not apply.
4. Dimensions b1 and c1 apply to lead base metal only. Dimension M applies to lead plating and finish thickness. The maximum limits of lead dimensions b and c or M shall be measured at the centroid of the finished lead surfaces, when solder dip or tin plate lead finish is applied.
5. N is the maximum number of terminal positions.
6. Measure dimension S1 at all four corners.
7. For bottom brazed lead packages, no organic or polymeric materials shall be molded to the bottom of the package to cover the leads.
8. Dimension Q shall be measured at the point of exit (beyond the meniscus) of the lead from the body. Dimension Q minimum shall be reduced by 0.0015 inch (0.038 mm) maximum when solder dip lead finish is applied.

FIGURE 1. Case outline – Continued.

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Device types	01, 02, 03, and 04	
Case outline	X	
Terminal number	Terminal symbol	Description
1	DNC	Do not connect.
2	V _{IN}	Input voltage connection.
3	COMP	Compensation and noise reduction capacitor.
4	GND	Ground connection.
5	TRIM	Voltage reference trim input.
6	V _{OUT}	Voltage reference output.
7	DNC	Do not connect.
8	DNC	Do not connect.
Package lid		Package lid is internally connected to pin 4 (GND).

FIGURE 2. Terminal connections.

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4. VERIFICATION

4.1 Sampling and inspection. For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein.

4.2 Screening. For device classes Q and V, screening shall be in accordance with MIL-PRF-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection.

4.2.1 Additional criteria for device classes Q and V.

- a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1015 of MIL-STD-883.
- b. Interim and final electrical test parameters shall be as specified in table IIA herein.
- c. Additional screening for device class V beyond the requirements of device class Q shall be as specified in MIL-PRF-38535, appendix B.

4.3 Qualification inspection for device classes Q and V. Qualification inspection for device classes Q and V shall be in accordance with MIL-PRF-38535. Inspections to be performed shall be those specified in MIL-PRF-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

4.4 Conformance inspection. Technology conformance inspection for classes Q and V shall be in accordance with MIL-PRF-38535 including groups A, B, C, D, and E inspections, and as specified herein.

4.4.1 Group A inspection.

- a. Tests shall be as specified in table IIA herein.
- b. Subgroups 4, 5, 6, 7, 8, 9, 10, and 11 in table I, method 5005 of MIL-STD-883 shall be omitted.

4.4.2 Group C inspection. The group C inspection end-point electrical parameters shall be as specified in table IIA herein.

4.4.2.1 Additional criteria for device classes Q and V. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1005 of MIL-STD-883.

4.4.3 Group D inspection. The group D inspection end-point electrical parameters shall be as specified in table IIA herein.

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TABLE IIA. Electrical test requirements.

Test requirements	Subgroups (in accordance with MIL-PRF-38535, table III)	
	Device class Q	Device class V
Interim electrical parameters (see 4.2)	1	1
Final electrical parameters (see 4.2)	1,2,3 <u>1/</u>	1,2,3 <u>1/</u> <u>2/</u>
Group A test requirements (see 4.4)	1,2,3	1,2,3
Group C end-point electrical parameters (see 4.4)	1,2,3	1,2,3 <u>2/</u>
Group D end-point electrical parameters (see 4.4)	1	1
Group E end-point electrical parameters (see 4.4)	1	1

1/ PDA applies to subgroup 1 for device class Q and subgroup 1 and Δ for device class V.

2/ Delta limits as specified in table IIB shall be required where specified, and the delta limits shall be completed with reference to the zero hour electrical parameters (see table IA).

TABLE IIB. Burn-in and life test delta parameters. (TA = +25°C). 1/

Parameters	Symbol	Device type	Min	Max	Units
VOUT accuracy	VOA	01	-1.00	1.00	mV
		02	-1.25	1.25	
		03	-2.50	2.50	
		04	-3.75	3.75	
Supply current	IIN	01, 02, 03, 04	-100	100	μA

1/ Deltas are performed at room temperature.

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4.4.4 Group E inspection. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein).

- a. End-point electrical parameters shall be as specified in table IIA herein.
- b. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535 for the RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as defined in table IA at TA = +25°C ±5°C, after exposure, to the subgroups specified in table IIA herein.

4.4.4.1 Total dose irradiation testing. Total dose irradiation testing shall be performed in accordance with MIL-STD-883 method 1019, condition A and as specified herein. In addition, a low dose rate test shall be performed in accordance with MIL-STD-883 method 1019, condition D and as specified herein.

4.4.4.2 Single event phenomena (SEP). When specified in the purchase order or contract, SEP testing shall be performed on class V devices. SEP testing shall be performed on the Standard Evaluation Circuit (SEC) or alternate SEP test vehicle as approved by the qualifying activity at initial qualification and after any design or process changes which may affect the upset or latchup characteristics. Test four devices with zero failures. ASTM F1192 may be used as a guideline when performing SEP testing. The recommended test conditions for SEP are as follows:

- a. The ion beam angle of incidence shall be between normal to the die surface and 60° to the normal, inclusive (i.e. 0° ≤ angle ≤ 60°). No shadowing of the ion beam due to fixturing or package related affects is allowed.
- b. The fluence shall be ≥ 100 errors or ≥ 10⁷ ions/cm².
- c. The flux shall be between 10² and 10⁵ ions/cm²/s. The cross-section shall be verified to be flux independent by measuring the cross-section at two flux rates which differ by at least an order of magnitude.
- d. The particle range shall be ≥ 20 micron in silicon.
- e. The test temperature shall be +25°C ±10% for SET. The test temperature shall be +125°C ±10% for SEB and SEL.
- f. Bias conditions shall be VIN = 36 V maximum for the latchup measurements.
- g. For SEL, SEB, and SET test limits, see table IB herein.

5. PACKAGING

5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-PRF-38535 for device classes Q and V.

6. NOTES

6.1 Intended use. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.

6.1.1 Replaceability. Microcircuits covered by this drawing will replace the same generic device covered by a contractor prepared specification or drawing.

6.2 Configuration control of SMD's. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished using DD Form 1692, Engineering Change Proposal.

6.3 Record of users. Military and industrial users should inform DLA Land and Maritime when a system application requires configuration control and which SMD's are applicable to that system. DLA Land and Maritime will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DLA Land and Maritime-VA, telephone (614) 692-8108.

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6.4 Comments. Comments on this drawing should be directed to DLA Land and Maritime-VA, Columbus, Ohio 43218-3990, or telephone (614) 692-0540.

6.5 Abbreviations, symbols, and definitions. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535 and MIL-HDBK-1331.

6.6 Sources of supply.

6.6.1 Sources of supply for device classes Q and V. Sources of supply for device classes Q and V are listed in MIL-HDBK-103 and QML-38535. The vendors listed in MIL-HDBK-103 and QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DLA Land and Maritime-VA and have agreed to this drawing.

6.7 Additional information. When applicable, a copy of the following additional data shall be maintained and available from the device manufacturer:

- a. RHA upset levels.
- b. Test conditions (SEP).
- c. Number of burnouts (SEB).
- d. Number of transients (SET).

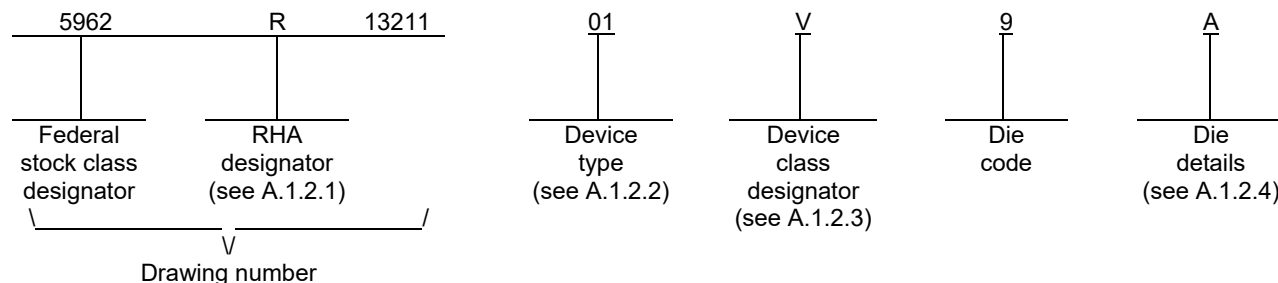
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A.1 SCOPE

A.1.1 Scope. This appendix establishes minimum requirements for microcircuit die to be supplied under the Qualified Manufacturers List (QML) Program. QML microcircuit die meeting the requirements of MIL-PRF-38535 and the manufacturers approved QM plan for use in monolithic microcircuits, multi-chip modules (MCMs), hybrids, electronic modules, or devices using chip and wire designs in accordance with MIL-PRF-38534 are specified herein. Two product assurance classes consisting of military high reliability (device class Q) and space application (device class V) are reflected in the Part or Identification Number (PIN). When available, a choice of Radiation Hardiness Assurance (RHA) levels are reflected in the PIN.

A.1.2 PIN. The PIN is as shown in the following example:



A.1.2.1 RHA designator. Device classes Q and V RHA identified die meet the MIL-PRF-38535 specified RHA levels. A dash (-) indicates a non-RHA die.

A.1.2.2 Device type(s). The device type(s) identify the circuit function as follows:

<u>Device type</u>	<u>Generic number</u>	<u>Voltage reference output</u>	<u>Circuit function</u>
01	ISL71090SEH-12	1.25 V	Radiation hardened ultra low noise, precision voltage reference
02	ISL71090SEH-25	2.5 V	Radiation hardened ultra low noise, precision voltage reference
03	ISL71090SEH-50	5.0 V	Radiation hardened ultra low noise, precision voltage reference
04	ISL71090SEH-75	7.5 V	Radiation hardened ultra low noise, precision voltage reference

A.1.2.3 Device class designator.

<u>Device class</u>	<u>Device requirements documentation</u>
Q or V	Certification and qualification to the die requirements of MIL-PRF-38535

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A.1.2.4 Die details. The die details designation is a unique letter which designates the die's physical dimensions, bonding pad location(s) and related electrical function(s), interface materials, and other assembly related information, for each product and variant supplied to this appendix.

A.1.2.4.1 Die physical dimensions.

<u>Die type</u>	<u>Figure number</u>
01, 02, 03, 04	A-1

A.1.2.4.2 Die bonding pad locations and electrical functions.

<u>Die type</u>	<u>Figure number</u>
01, 02, 03, 04	A-1

A.1.2.4.3 Interface materials.

<u>Die type</u>	<u>Figure number</u>
01, 02, 03, 04	A-1

A.1.2.4.4 Assembly related information.

<u>Die type</u>	<u>Figure number</u>
01, 02, 03, 04	A-1

A.1.3 Absolute maximum ratings. See paragraph 1.3 herein for details.

A.1.4 Recommended operating conditions. See paragraph 1.4 herein for details.

A.1.5 Radiation features. See paragraph 1.5 herein for details.

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A.2 APPLICABLE DOCUMENTS.

A.2.1 Government specification, standards, and handbooks. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATION

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

DEPARTMENT OF DEFENSE STANDARD

MIL-STD-883 - Test Method Standard Microcircuits.

DEPARTMENT OF DEFENSE HANDBOOKS

MIL-HDBK-103 - List of Standard Microcircuit Drawings.

MIL-HDBK-780 - Standard Microcircuit Drawings.

(Copies of these documents are available online at <https://quicksearch.dla.mil>.)

A.2.2 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

A.3 REQUIREMENTS

A.3.1 Item requirements. The individual item requirements for device classes Q and V shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein.

A.3.2 Design, construction and physical dimensions. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein and the manufacturer's QM plan for device classes Q and V.

A.3.2.1 Die physical dimensions. The die physical dimensions shall be as specified in A.1.2.4.1 and on figure A-1.

A.3.2.2 Die bonding pad locations and electrical functions. The die bonding pad locations and electrical functions shall be as specified in A.1.2.4.2 and on figure A-1.

A.3.2.3 Interface materials. The interface materials for the die shall be as specified in A.1.2.4.3 and on figure A-1.

A.3.2.4 Assembly related information. The assembly related information shall be as specified in A.1.2.4.4 and on figure A-1.

A.3.2.5 Radiation exposure circuit. The radiation exposure circuit shall be as defined in paragraph 3.2.3 herein.

A.3.3 Electrical performance characteristics and post-irradiation parameter limits. Unless otherwise specified herein, the electrical performance characteristics and post-irradiation parameter limits are as specified in table IA of the body of this document.

A.3.4 Electrical test requirements. The wafer probe test requirements shall include functional and parametric testing sufficient to make the packaged die capable of meeting the electrical performance requirements in table IA.

A.3.5 Marking. As a minimum, each unique lot of die, loaded in single or multiple stack of carriers, for shipment to a customer, shall be identified with the wafer lot number, the certification mark, the manufacturer's identification and the PIN listed in A.1.2 herein. The certification mark shall be a "QML" or "Q" as required by MIL-PRF-38535.

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A.3.6 Certification of compliance. For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see A.6.4 herein). The certificate of compliance submitted to DLA Land and Maritime –VA prior to listing as an approved source of supply for this appendix shall affirm that the manufacturer’s product meets, for device classes Q and V, the requirements of MIL-PRF-38535 and the requirements herein.

A.3.7 Certificate of conformance. A certificate of conformance as required for device classes Q and V in MIL-PRF-38535 shall be provided with each lot of microcircuit die delivered to this drawing.

A.4 VERIFICATION

A.4.1 Sampling and inspection. For device classes Q and V, die sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer’s Quality Management (QM) plan. The modifications in the QM plan shall not affect the form, fit, or function as described herein.

A.4.2 Screening. For device classes Q and V, screening shall be in accordance with MIL-PRF-38535, and as defined in the manufacturer’s QM plan. As a minimum, it shall consist of:

- a. Wafer lot acceptance for class V product using the criteria defined in MIL-STD-883, method 5007.
- b. 100% wafer probe (see paragraph A.3.4 herein).
- c. 100% internal visual inspection to the applicable class Q or V criteria defined in MIL-STD-883, method 2010 or the alternate procedures allowed in MIL-STD-883, method 5004.

A.4.3 Conformance inspection.

A.4.3.1 Group E inspection. Group E inspection is required only for parts intended to be identified as radiation assured (see A.3.5 herein). RHA levels for device classes Q and V shall be as specified in MIL-PRF-38535. End point electrical testing of packaged die shall be as specified in table IIA herein. Group E tests and conditions are as specified in paragraphs 4.4.4, 4.4.4.1, and 4.4.4.2 herein.

A.5 DIE CARRIER

A.5.1 Die carrier requirements. The requirements for the die carrier shall be accordance with the manufacturer’s QM plan or as specified in the purchase order by the acquiring activity. The die carrier shall provide adequate physical, mechanical and electrostatic protection.

A.6 NOTES

A.6.1 Intended use. Microcircuit die conforming to this drawing are intended for use in microcircuits built in accordance with MIL-PRF-38535 or MIL-PRF-38534 for government microcircuit applications (original equipment), design applications, and logistics purposes.

A.6.2 Comments. Comments on this appendix should be directed to DLA Land and Maritime –VA, Columbus, Ohio, 43218-3990 or telephone (614)-692-0540.

A.6.3 Abbreviations, symbols, and definitions. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535 and MIL-HDBK-1331.

A.6.4 Sources of supply for device classes Q and V. Sources of supply for device classes Q and V are listed in QML-38535. The vendors listed within MIL-HDBK-103 and QML-38535 have submitted a certificate of compliance (see A.3.6 herein) to DLA Land and Maritime –VA and have agreed to this drawing.

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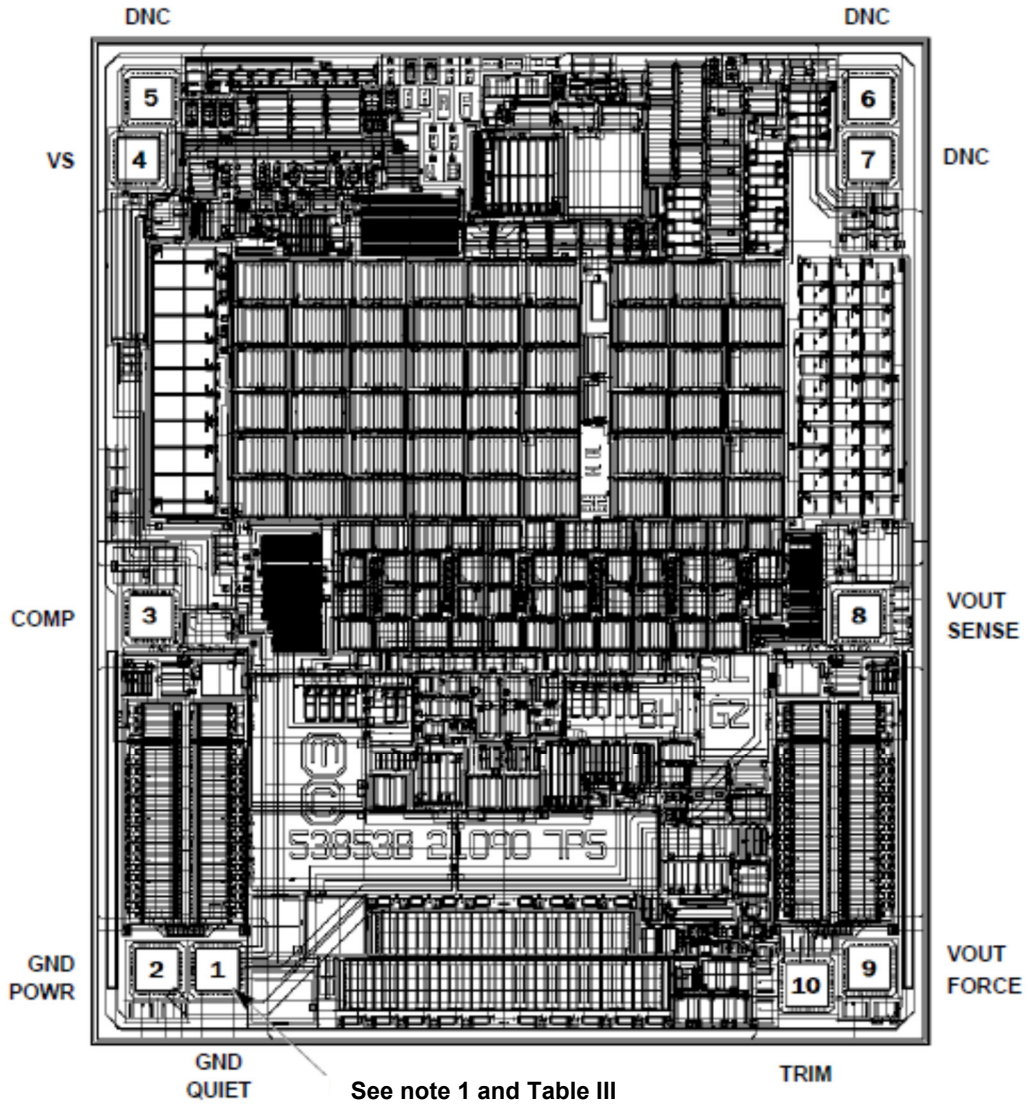


FIGURE A-1. Die bonding pad locations and electrical functions.

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TABLE III. Die plot.

Pad name	Pad number	X (μm)	Y (μm)	Bond wires per pad
GND QUIET	1	0	0	1
GND PWR	2	-104	0	1
COMP	3	-108	589	1
VS	4	-125	1350	1
DNC	5	-108	1452	1
DNC	6	1089	1452	1
DNC	7	1089	1350	1
VOUT SENSE	8	1072	598	1
VOUT FORCE	9	1088	1	1
TRIM	10	985	-25	1

NOTES:

1. Origin of coordinates is the centroid of GND QUIET.
2. Bond wire size is 1.0 mil.

Die bonding pad locations and electrical functions

Die physical dimensions.

Die size: 1464 μm x 1744 μm (58 mils x 69 mils)

Die thickness: 483 μm \pm 25.4 μm (19.0 mils \pm 1 mil)

Interface materials.

Top metallization: AlCu (99.5%/0.5%)

Thickness: 30 kÅ

Backside metallization: None - Silicon

Glassivation.

Type: Nitrox

Thickness: 15 kÅ

Substrate: PR40: Bonded wafer dielectrically isolated complementary bipolar

Assembly related information.

Substrate potential: Floating

Special assembly instructions:

GND QUIET (pad 1) and GND PWR (pad 2) must both be connected/bonded to GND.

VOUT SENSE (pad 8) and VOUT FORCE (pad 9) must both be connected/bonded to VOUT .

FIGURE A-1. Die bonding pad locations and electrical functions - continued.

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STANDARD MICROCIRCUIT DRAWING BULLETIN

DATE: 20-05-12

Approved sources of supply for SMD 5962-13211 are listed below for immediate acquisition information only and shall be added to MIL-HDBK-103 and QML-38535 during the next revision. MIL-HDBK-103 and QML-38535 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DLA Land and Maritime-VA. This information bulletin is superseded by the next dated revision of MIL-HDBK-103 and QML-38535. DLA Land and Maritime maintains an online database of all current sources of supply at <https://landandmaritimeapps.dla.mil/programs/smcr/>.

Standard microcircuit drawing PIN <u>1/</u>	Vendor CAGE number	Vendor similar PIN <u>2/</u>
5962R1321101VXC	34371	ISL71090SEHVF12
5962R1321102VXC	34371	ISL71090SEHVF25
5962R1321103VXC	34371	ISL71090SEHVF50
5962R1321104VXC	34371	ISL71090SEHVF75
5962R1321101V9A	34371	ISL71090SEHVX12
5962R1321102V9A	34371	ISL71090SEHVX25
5962R1321103V9A	34371	ISL71090SEHVX50
5962R1321104V9A	34371	ISL71090SEHVX75

1/ The lead finish shown for each PIN representing a hermetic package is the most readily available from the manufacturer listed for that part. If the desired lead finish is not listed contact the vendor to determine its availability.

2/ Caution. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.

Vendor CAGE
number

34371

Vendor name
and address

Renesas Electronics America
1650 Robert J. Conlan Blvd. NE
Palm Bay, FL 32905-3406

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